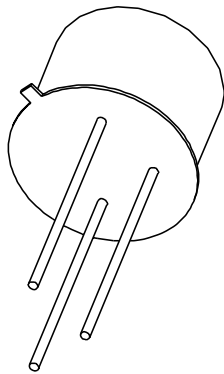


DATA SHEET



BSV64

NPN medium power transistor

Product specification
Supersedes data of 1997 Apr 21
File under Discrete Semiconductors, SC04

1997 Sep 04

NPN medium power transistor

BSV64

FEATURES

- High current (max. 2 A)
- Low voltage (max. 60 V)
- Good high current saturation characteristics.

APPLICATIONS

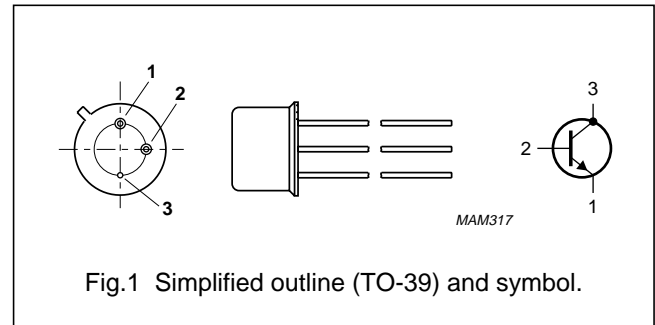
- General purpose switching and amplification
- Print hammer driver.

DESCRIPTION

NPN medium power transistor in a TO-39 metal package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	100	V
V_{CEO}	collector-emitter voltage	open base	–	–	60	V
I_{CM}	peak collector current		–	–	5	A
P_{tot}	total power dissipation	$T_{case} \leq 50\text{ }^{\circ}\text{C}$	–	–	5	W
h_{FE}	DC current gain	$I_C = 2\text{ A}; V_{CE} = 2\text{ V}$	40	–	–	
f_T	transition frequency	$I_C = 0.5\text{ A}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	–	100	–	MHz

NPN medium power transistor

BSV64

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	100	V
V_{CEO}	collector-emitter voltage	open base	–	60	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	2	A
I_{CM}	peak collector current		–	5	A
I_{BM}	peak base current		–	500	mA
P_{tot}	total power dissipation	$T_{case} \leq 50\text{ °C}$	–	5	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	175	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	thermal resistance from junction to case	25	K/W

CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	–	10	μA
h_{FE}	DC current gain	$I_C = 2\text{ A}; V_{CE} = 2\text{ V}$	40	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 5\text{ A}; I_B = 0.5\text{ A}$	–	–	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 5\text{ A}; I_B = 0.5\text{ A}$	–	–	1.8	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	80	pF
f_T	transition frequency	$I_C = 0.5\text{ A}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	–	100	–	MHz
Switching times (between 10% and 90% levels)						
t_{on}	turn on time	$I_{Con} = 5\text{ A}; I_{Bon} = 500\text{ mA};$	–	–	0.6	μs
t_{off}	turn-off time	$I_{Boff} = -500\text{ mA}$	–	–	1.2	μs

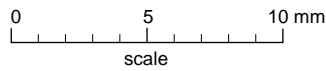
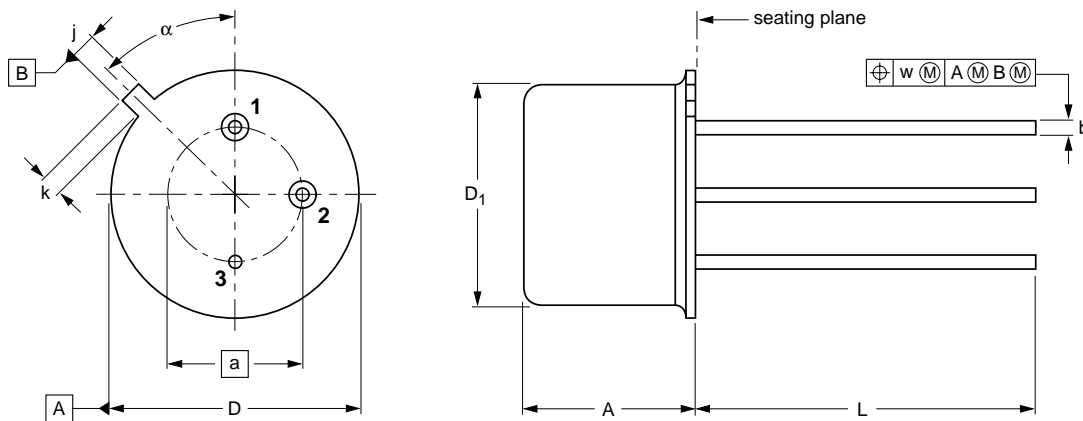
NPN medium power transistor

BSV64

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D ₁	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

NPN medium power transistor

BSV64

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NPN medium power transistor

BSV64

NOTES

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NOTES

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